Abstracts

Extension of Existing Models to Ion-Implanted MESFET's

P. de Santis. "Extension of Existing Models to Ion-Implanted MESFET's." 1980 Transactions on Microwave Theory and Techniques 28.6 (Jun. 1980 [T-MTT]): 638-647.

This work extends uniform MESFET's models to MESFET's with arbitrary doping density profiles. Numerical computations have carried out for ion-implanted devices with a Gaussian doping density profile. Good agreement is found between theory and experiment.

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